

SEMICONDUCTOR MEMORY DEVICE AND FABRICATION METHOD THEREOF USING DAMASCENE BITLINE PROCESS

ABSTRACT OF THE DISCLOSURE

5 A semiconductor memory device includes a silicon substrate with a gate and contact pads at both sides of the gate, an inter-insulation layer formed on the substrate, including a storage node contact and a bit-line contact exposing a corresponding contact pad, and including a groove-shaped bit-line pattern, a storage node contact plug formed in the storage node contact, and a damascene bit line formed within the bit-line pattern and connected with
10 the exposed corresponding contact pad through the bit-line contact.

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